

IN THE CLAIMS:

Please amend claims 1-3 and 13 as follows:

1. (currently amended) A method for contact opening definition for active element electrical connections, said method comprising the steps of:

forming a layer of BPSG on a surface of an integrated circuit; and  
forming a transparent layer of nitride UV above the layer of BPSG; and  
after the step of forming the transparent layer of nitride UV, etching the  
transparent layer of nitride UV so as to form at least one contact opening.

2. (currently amended) The method according to claim 1, further comprising the step of:

after the step of forming a transparent layer of nitride UV and before the etching  
step, forming two overlapped layers of BARC and resist on the surface of the integrated  
circuit.

3. (currently amended) The method according to claim 2, further comprising  
wherein the etching step of: is performed after the step of forming two overlapped layers  
of BARC and resist, chemically etching the integrated circuit so as to form contact  
openings.

4. (original) The method according to claim 3, further comprising the step of:  
before the step of forming a layer of BPSG, forming a USG oxide layer on the surface of the integrated circuit, the USG oxide layer having a thickness of between about 500Å and 2500Å.

5. (original) The method according to claim 1, further comprising the step of:  
before the step of forming a layer of BPSG, forming a USG oxide layer on the surface of the integrated circuit, the USG oxide layer having a thickness of between about 500Å and 2500Å.

6. (original) The method according to claim 1, wherein in the step of forming the transparent layer of nitride UV, the transparent layer of nitride UV is formed by deposition using an HDP process.
7. (original) The method according to claim 6, wherein the transparent layer of nitride UV has a thickness of between about 100Å and 500Å.
8. (original) The method according to claim 1, wherein in the step of forming the transparent layer of nitride UV, the transparent layer of nitride UV is formed by deposition using a CVD process.
9. (original) The method according to claim 8, wherein the transparent layer of nitride UV has a thickness of between about 100Å and 500Å.
10. (original) The method according to claim 1, wherein the transparent layer of nitride UV has a thickness of less than about 500Å.
11. (original) The method according to claim 1, wherein the transparent layer of nitride UV has a thickness of between about 100Å and 500Å.
12. (original) The method according to claim 1, wherein the transparent layer of nitride UV has a thickness of between about 200Å and 500Å.
13. (currently amended) A machine-readable medium encoded with a program for contact opening definition for active element electrical connections, said program containing instructions for performing the steps of:  
forming a layer of BPSG on a surface of an integrated circuit; and  
forming a transparent layer of nitride UV above the layer of BPSG; and  
after the step of forming the transparent layer of nitride UV, etching the  
transparent layer of nitride UV so as to form at least one contact opening.

14. (original) The machine-readable medium according to claim 13, wherein the program further contains instructions for performing the step of:  
after the step of forming a transparent layer of nitride UV, forming two overlapped layers of BARC and resist on the surface of the integrated circuit.

15. (original) The machine-readable medium according to claim 13, wherein the program further contains instructions for performing the step of:  
before the step of forming a layer of BPSG, forming a USG oxide layer on the surface of the integrated circuit, the USG oxide layer having a thickness of between about 500Å and 2500Å.

16. (original) The machine-readable medium according to claim 13, wherein in the step of forming the transparent layer of nitride UV, the transparent layer of nitride UV is formed by deposition using an HDP process.

17. (original) The machine-readable medium according to claim 13, wherein in the step of forming the transparent layer of nitride UV, the transparent layer of nitride UV is formed by deposition using a CVD process.

18. (original) The machine-readable medium according to claim 13, wherein the transparent layer of nitride UV has a thickness of less than about 500Å.

19. (original) The machine-readable medium according to claim 13, wherein the transparent layer of nitride UV has a thickness of between about 100Å and 500Å.